

# **PMDPB70XPE** 20 V dual P-channel Trench MOSFET Rev. 1 — 20 June 2012

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Dual small-signal P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology

### 1.3 Applications

- Relay driver
- High-speed line driver

- 2 kV ElectroStatic Discharge (ESD) protection
- High-side load switch
- Switching circuits

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	<u>[1]</u>	-	-	-4.2	А
Static charac	cteristics (per transistor)						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 25 °C		-	66	79	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



#### 20 V dual P-channel Trench MOSFET

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		
2	G1	gate TR1	6 5 4	
3	D2	drain TR2		
4	S2	source TR2	7 8	$G1 \left( \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	
7	D1	drain TR1	Transparent top view	S1 S2 017aaa260
8	D2	drain TR2	DFN2020-6 (SOT1118)	

### 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMDPB70XPE	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118			

### 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PMDPB70XPE	2B

### 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub> drain current	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	<u>[1]</u>	-	-4.2	А
		$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	<u>[1]</u>	-	-3	А
		$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-2.1	А
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C}$ ; single pulse; $t_p \le 10 \mu\text{s}$		-	-12	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	515	mW
			[1]	-	1210	mW
		T <sub>sp</sub> = 25 °C		-	8330	mW
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-1.3	А
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#### Table 5. Limiting values ... continued

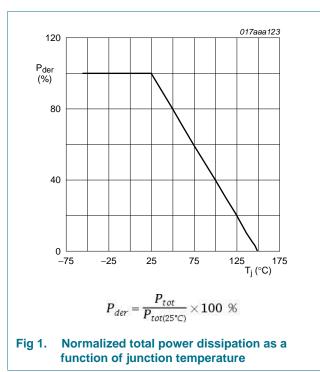
In accordance with the Absolute Maximum Rating System (IEC 60134).

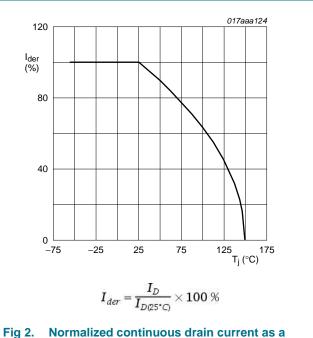
Symbol	Parameter	Conditions		Min	Мах	Unit
ESD maxim	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 kΩ	[3]	-	2000	V
Per device						
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

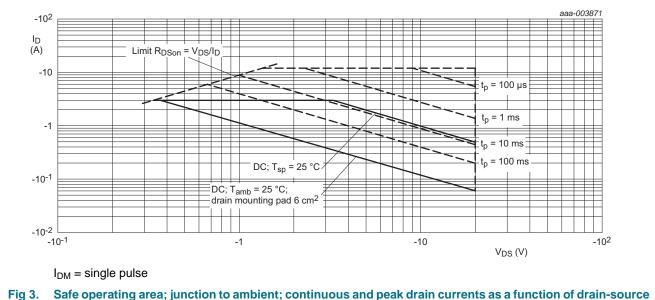






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### 6. Thermal characteristics

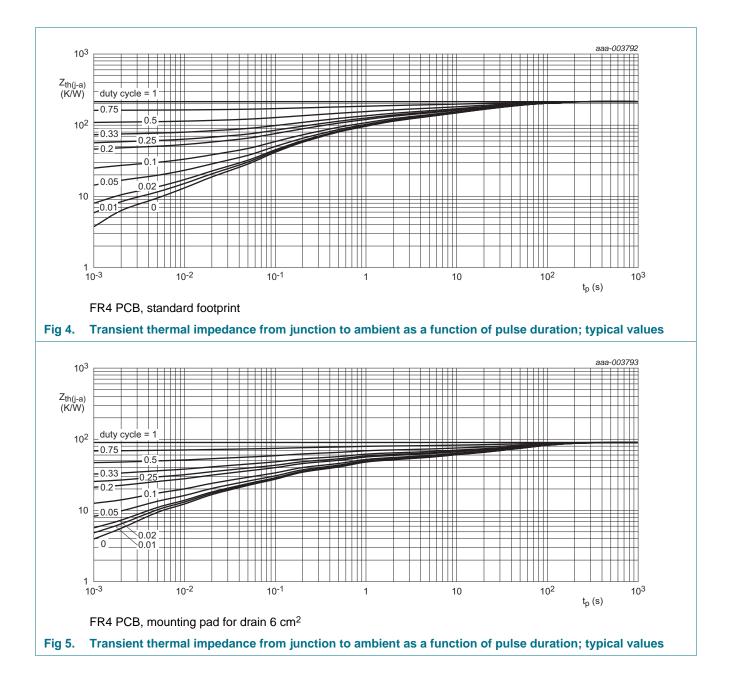
#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	r						
R <sub>th(j-a)</sub> thermal resistance		in free air	<u>[1]</u>	-	212	244	K/W
	from junction to ambient		[2]	-	90	104	K/W
		in free air; t ≤ 5 s	[2]	-	55	64	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	11	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

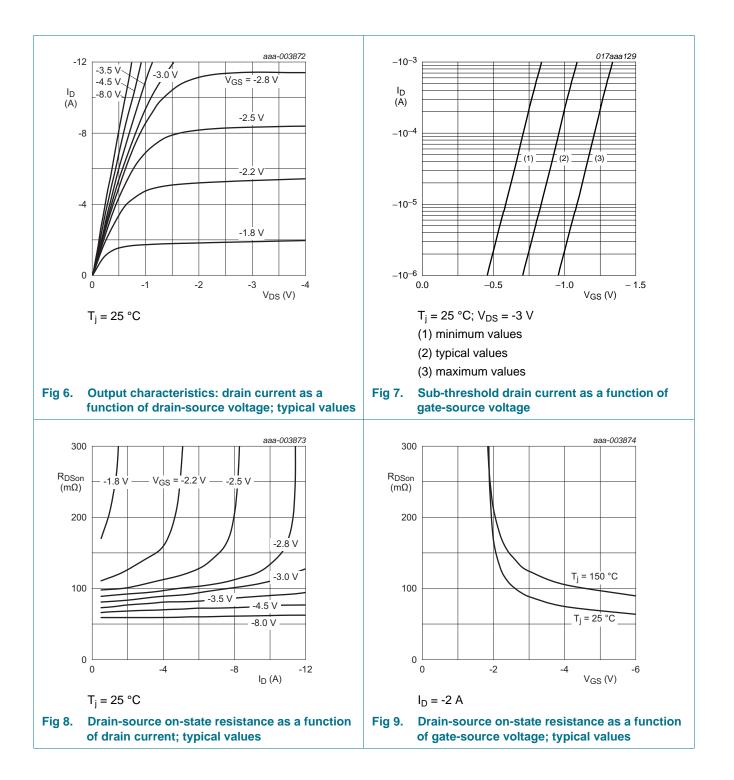
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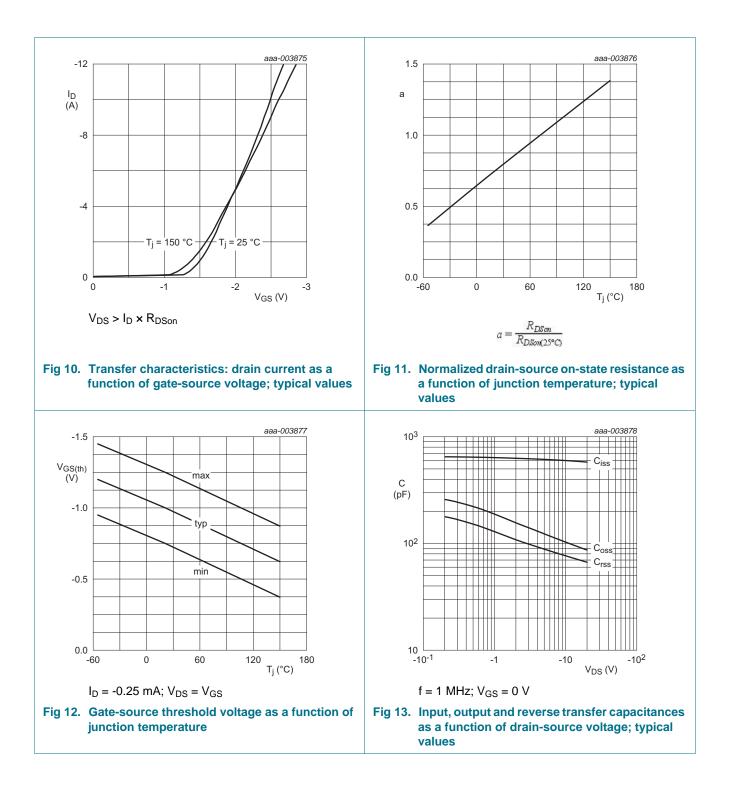
### 20 V dual P-channel Trench MOSFET

### 7. Characteristics

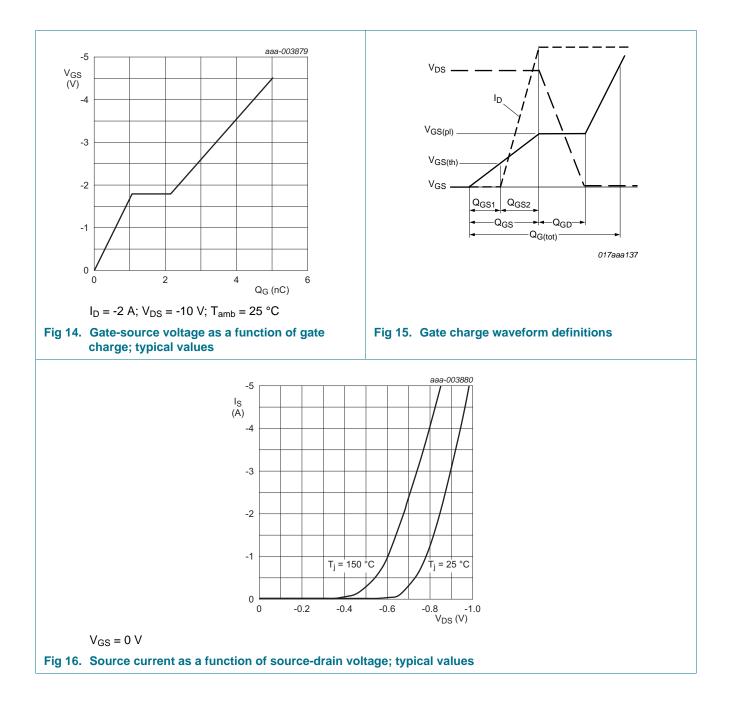
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	-20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.75	-1	-1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μA
		$V_{GS} = -12 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	-10	μA
R <sub>DSon</sub>		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 25 °C	-	66	79	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -2 A; T <sub>j</sub> = 150 °C	-	94	112	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -1.5 A; T <sub>j</sub> = 25 °C	-	98	123	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_D$ = -2 A; $T_j$ = 25 °C	-	7.3	-	S
Dynamic c	haracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -2 A; $V_{GS}$ = -4.5 V;	-	5	7.5	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.1	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	600	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	103	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	77	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -2 A; $V_{GS}$ = -4.5 V;	-	7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	16	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	33	-	ns
t <sub>f</sub>	fall time		-	15	-	ns
Source-dra	ain diode (per transistor)					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.5 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V



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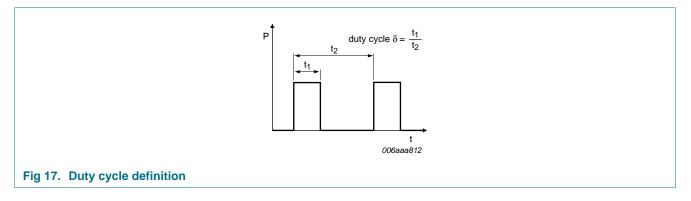


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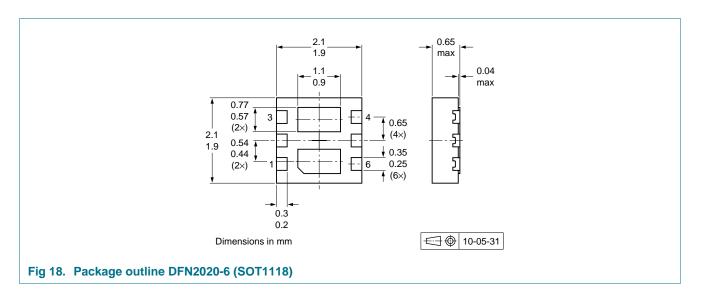


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### 8. Test information

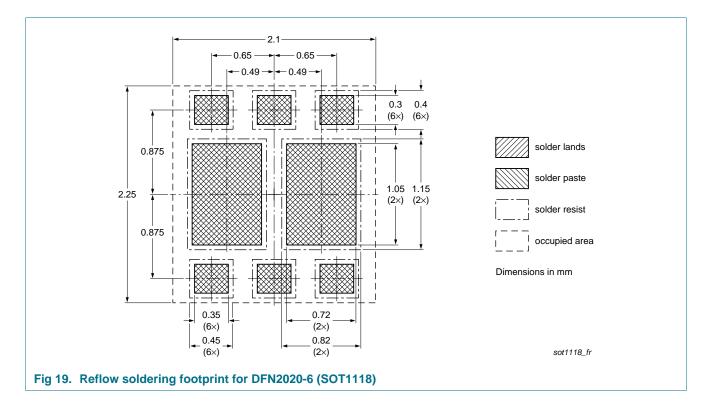


### 9. Package outline



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### **10. Soldering**



### 20 V dual P-channel Trench MOSFET

### **11. Revision history**

Table 8. Revi	Fable 8.         Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PMDPB70XPE v	.1 20120620	Product data sheet	-	-		

### 12. Legal information

### **12.1 Data sheet status**

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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